

Form PTO 1449 U.S. Department of Commerce Patent and Trademark Office Information Disclosure Statement by Applicant	ATTY. DOCKET NUMBER NITT.0191	SERIAL NUMBER To be Assigned 10/77707
	APPLICANT Sato et al.	
	FILING DATE Concurrently Herewith	GROUP

U.S. Patent Documents

Examiner Initial	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE

Foreign Patent Documents

Examiner Initial	DOCUMENT NUMBER	FILING DATE	COUNTRY	CLASS	SUB-CLASS	TRANSLATION	
						Yes	No
GA	2003-78213	9/5/2001	Japan			Abstract	X
GA	2001-102355	7/26/2000	Japan			Abstract	X
GA	10-335756	6/5/97	Japan			Abstract	X

Other Documents (Including Author, Title, Date Pertinent Pages, Etc.)

SA	M. Aoki et al., "85°C-10Gbit/s Operation of 1.30µm InGaAlAs MQW-DFB Laser", 26 th European conference (ECOC2000), Vol 1, 2 pages
I	P.J.A. Thijs et al., "High Performance Buried Heterostructure λ = 1.5 µm InGaAs/AlGaInAs Strained-Layer Quantum Well Laser Diodes", International Conference on Indium Phosphide and Related Materials, Conference Proceedings 1996, pp. 765-768
I	K. Shinoda et al., "Highly Reliable InGaAsP/InP Lasers with Defect-Free Regrowth Interfaces formed by Newly Composed HBr-Based Solutions", 2001 IEEE, 2001 International Conference on Indium Phosphide and Related Materials, pp. 409-412
SA	D. Bertone et al., "High Reliability, High Yield, High Modulation Bandwidth, Low Threshold Current 1.55 µm MQW Laser by New In-Situ Etching Technique", 24 th European Conference on Optical Communication (ECOC 1998) Proceedings, Vol. 1, pp. 75-76

EXAMINER

Samuel

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